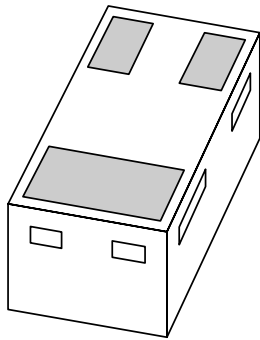


DATA SHEET



PBSS2540M

40 V, 0.5 A

NPN low V_{CEsat} (BISS) transistor

40 V, 0.5 A
NPN low V_{CEsat} (BISS) transistor

PBSS2540M

FEATURES

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High efficiency leading to reduced heat generation
- Reduced printed-circuit board requirements.

APPLICATIONS

- Power management:
 - DC-DC converter
 - Supply line switching
 - Battery charger
 - LCD backlighting.
- Peripheral driver:
 - Driver in low supply voltage applications (e.g. lamps and LEDs).
 - Inductive load drivers (e.g. relays, buzzers and motors).

DESCRIPTION

Low V_{CEsat} NPN transistor in a SOT883 leadless ultra small plastic package.
PNP complement: PBSS3540M.

MARKING

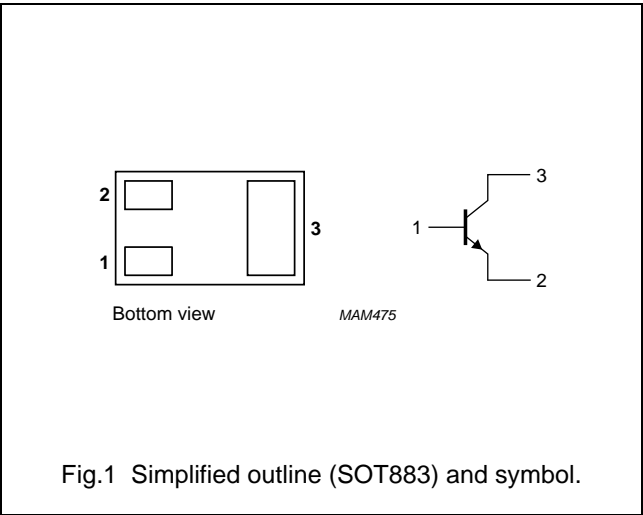
TYPE NUMBER	MARKING CODE
PBSS2540M	DC

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	40	V
I_C	collector current (DC)	500	mA
I_{CM}	peak collector current	1	A
R_{CEsat}	equivalent on-resistance	<500	m Ω

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	40	V
V_{CEO}	collector-emitter voltage	open base	–	40	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)	notes 1 and 2	–	500	mA
I_{CM}	peak collector current		–	1	A
I_{BM}	peak base current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; notes 1 and 2	–	250	mW
		$T_{amb} \leq 25\text{ °C}$; note 1 and 3	–	430	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Refer to SOT883 standard mounting conditions.
2. Device mounted on an FR4 printed-circuit board, single-sided copper, tinplated, standard footprint, with 60 μm copper strip line.
3. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm^2 .

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; notes 1 and 2	500	K/W
		in free air; notes 1, 3 and 4	290	K/W

Notes

1. Refer to SOT883 standard mounting conditions.
2. Device mounted on an FR4 printed-circuit board, single-sided copper, tinplated, standard footprint, with 60 μm copper strip line.
3. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm^2 .
4. Operated under pulsed conditions: duty cycle $\delta \leq 20\%$, pulse width $t_p \leq 30\text{ ms}$.

Soldering

Reflow soldering is the only recommended soldering method.

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CHARACTERISTICS $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

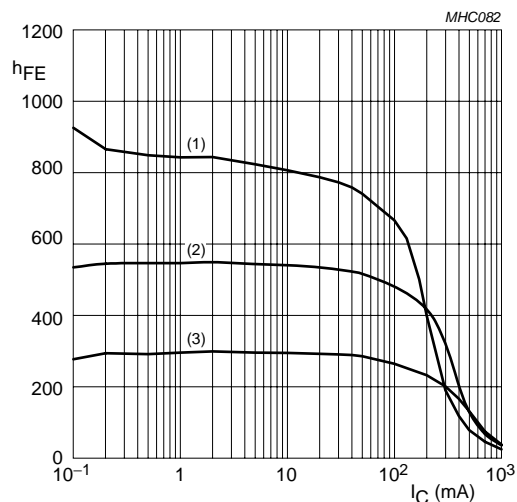
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0$	–	–	100	nA
		$V_{CB} = 30\text{ V}; I_E = 0; T_j = 150\text{ }^{\circ}\text{C}$	–	–	50	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0$	–	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 2\text{ V}; I_C = 10\text{ mA}$	200	–	–	
		$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}; \text{note 1}$	150	–	–	
		$V_{CE} = 2\text{ V}; I_C = 500\text{ mA}; \text{note 1}$	50	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	–	50	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	–	–	100	mV
		$I_C = 200\text{ mA}; I_B = 10\text{ mA}; \text{note 1}$	–	–	200	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	–	250	mV
R_{CEsat}	equivalent on-resistance	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	380	<500	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	–	1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}; \text{note 1}$	–	–	1.1	V
f_T	transition frequency	$I_C = 100\text{ mA}; V_{CE} = 5\text{ V};$ $f = 100\text{ MHz}$	250	450	–	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	–	6	pF

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

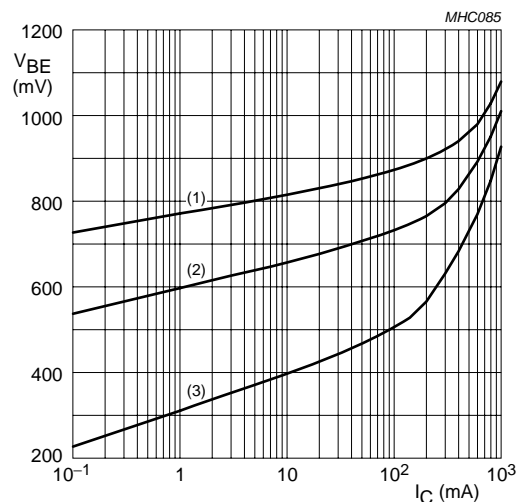
40 V, 0.5 A NPN low V_{CEsat} (BISS) transistor

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 $V_{CE} = 2 \text{ V.}$

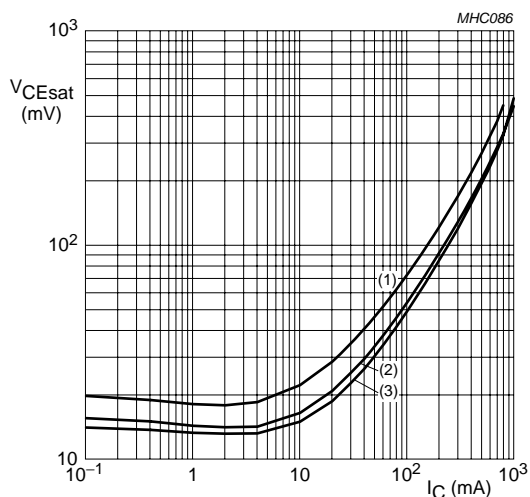
- (1) $T_{amb} = 150 \text{ }^{\circ}\text{C.}$
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C.}$
- (3) $T_{amb} = -55 \text{ }^{\circ}\text{C.}$

Fig.2 DC current gain as a function of collector current; typical values.

 $V_{CE} = 2 \text{ V.}$

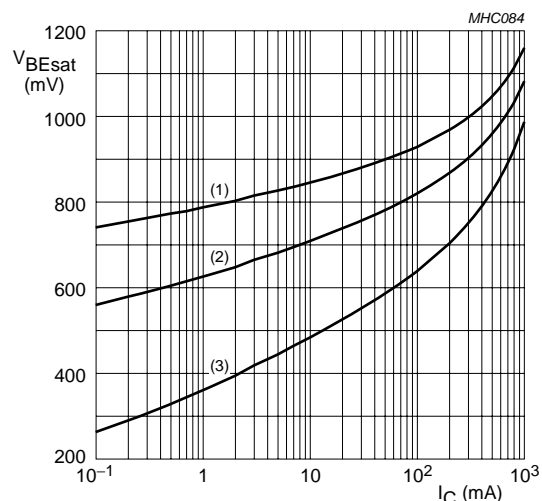
- (1) $T_{amb} = -55 \text{ }^{\circ}\text{C.}$
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C.}$
- (3) $T_{amb} = 150 \text{ }^{\circ}\text{C.}$

Fig.3 Base-emitter voltage as a function of collector current; typical values.

 $I_C/I_B = 20.$

- (1) $T_{amb} = 150 \text{ }^{\circ}\text{C.}$
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C.}$
- (3) $T_{amb} = -55 \text{ }^{\circ}\text{C.}$

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.

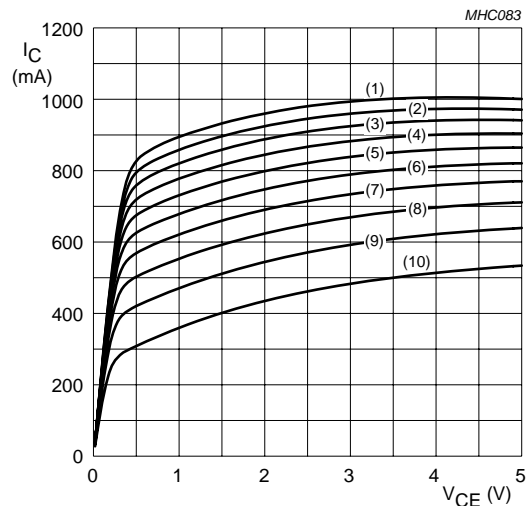
 $I_C/I_B = 20.$

- (1) $T_{amb} = 150 \text{ }^{\circ}\text{C.}$
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C.}$
- (3) $T_{amb} = -55 \text{ }^{\circ}\text{C.}$

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

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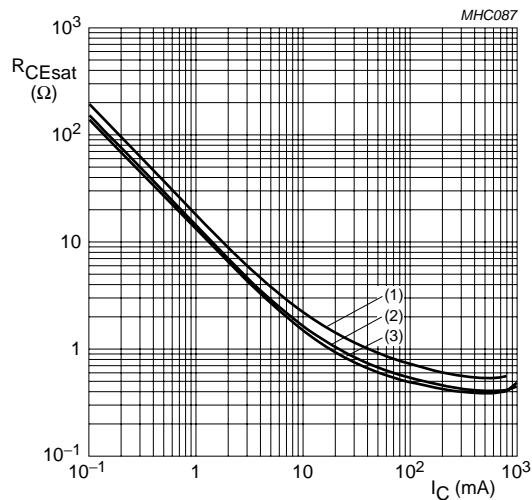
PBSS2540M



$T_{amb} = 25\text{ °C}$.

- | | | |
|------------------------------|------------------------------|------------------------------|
| (1) $I_B = 25\text{ mA}$. | (5) $I_B = 15\text{ mA}$. | (9) $I_B = 5\text{ mA}$. |
| (2) $I_B = 22.5\text{ mA}$. | (6) $I_B = 12.5\text{ mA}$. | (10) $I_B = 2.5\text{ mA}$. |
| (3) $I_B = 20\text{ mA}$. | (7) $I_B = 10\text{ mA}$. | |
| (4) $I_B = 17.5\text{ mA}$. | (8) $I_B = 7.5\text{ mA}$. | |

Fig.6 Collector current as a function of collector-emitter voltage; typical values.



$I_C/I_B = 20$.

- | |
|---------------------------------|
| (1) $T_{amb} = 150\text{ °C}$. |
| (2) $T_{amb} = 25\text{ °C}$. |
| (3) $T_{amb} = -55\text{ °C}$. |

Fig.7 Collector-emitter equivalent on-resistance as a function of collector current; typical values.

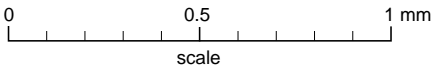
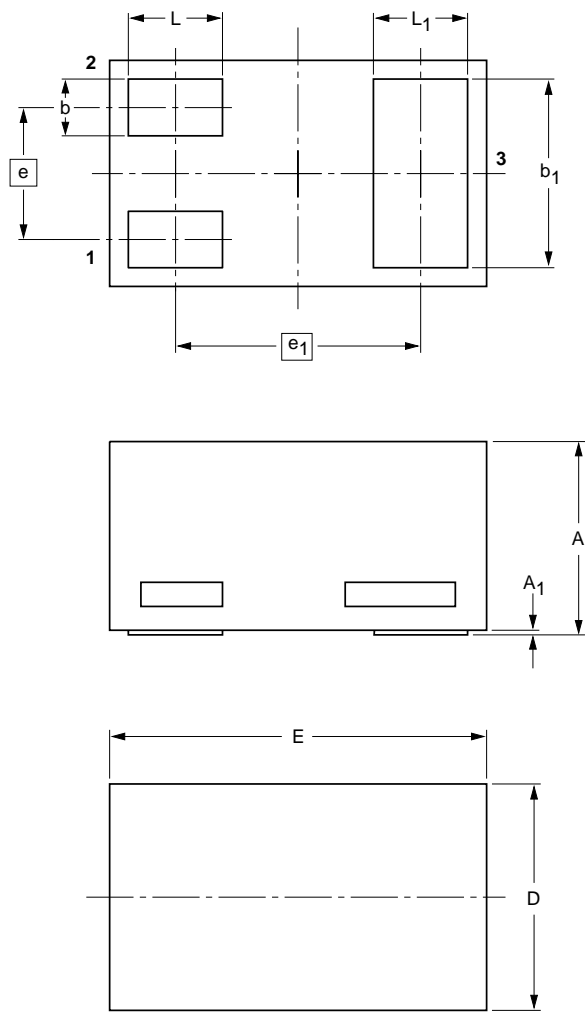
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PACKAGE OUTLINE

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883

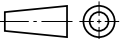


DIMENSIONS (mm are the original dimensions)

UNIT	A ⁽¹⁾	A ₁ max.	b	b ₁	D	E	e	e ₁	L	L ₁
mm	0.50 0.46	0.03	0.20 0.12	0.55 0.47	0.62 0.55	1.02 0.95	0.35	0.65	0.30 0.22	0.30 0.22

Note

1. Including plating thickness

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT883			SC-101			03-02-05 03-04-03

40 V, 0.5 A NPN low V_{CEsat} (BISS) transistor

PBSS2540M

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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